Abstracts

K- and Ka-band Power GaAs FETs

T. Noguchi and Y. Aono. "K- and Ka-band Power GaAs FETs." 1982 MTT-S International Microwave Symposium Digest 82.1 (1982 [MWSYM]): 156-158.

A deep-recess channel structure has been applied to high power FETs in order to improve performances above to K-band. Internally matched devices have exhibited 2W power output with 16% power-added efficiency at 18 GHz, and 165 mW with 3dB associated gain at 29.5 GHz.

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